

WHAT IS CLAIMED IS:

1. A display, having a reflective region, comprising:
a reflective material layer, formed on a region of a
5 substrate corresponding to said reflective region, having
a function for serving as a reflective layer;
an insulating layer formed on said reflective
material layer; and
a transparent electrode formed on said insulating
10 layer, wherein
said reflective material layer is formed by the same
layer as a layer having a prescribed function different
from said function for serving as said reflective layer.
- 15 2. The display according to claim 1, wherein
said reflective material layer has both of said
function for serving as said reflective layer and said
prescribed function different from said function for
serving as said reflective layer.
- 20 3. The display according to claim 2, wherein
said prescribed function different from said function
for serving as said reflective layer is a function for
serving as at least one layer selected from a group
25 consisting of a source/drain electrode, a gate electrode,

a storage capacitive electrode and a black matrix layer.

4. The display according to claim 2, wherein
said prescribed function different from said function
5 for serving as said reflective layer is a function for
serving as a gate electrode and a storage capacitive
electrode.

5. The display according to claim 1, further
10 comprising:

a thin-film transistor, formed between said
insulating layer and said substrate, having a pair of
source/drain regions, and
15 source/drain electrodes connected to said pair of
source/drain regions, wherein
said reflective material layer having said function
for serving as said reflective layer is formed by the same
layer as a layer constituting said source/drain electrodes.

20 6. The display according to claim 5, wherein
said reflective material layer having said function
for serving as said reflective layer is a layer
constituting at least either one of said source/drain
electrodes.

7. The display according to claim 1, further comprising a storage capacitor having a storage capacitive electrode, wherein

5 said reflective material layer having said function for serving as said reflective layer is formed by the same layer as a layer constituting a storage capacitive line of said storage capacitive electrode.

8. The display according to claim 1, further
10 comprising a thin-film transistor, formed between said insulating layer and said substrate, having a gate electrode, wherein

15 said reflective material layer having said function for serving as said reflective layer is formed by the same layer as a layer constituting said gate electrode.

9. The display according to claim 1, further comprising a black matrix layer formed between said insulating layer and said substrate, wherein
20 said reflective material layer is formed by the same layer as a layer constituting said black matrix layer.

10. The display according to claim 1, further comprising a transmissive region provided with no said
25 reflective material layer in addition to said reflective

region.

11. The display according to claim 10, further comprising:

5 a counter substrate provided oppositely to said substrate, and

a convex insulating layer provided on a region of said counter substrate corresponding to said reflective region.

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12. The display according to claim 11, further comprising a liquid crystal layer provided between said substrate and said counter substrate, wherein

15 the thickness of said convex insulating layer is so set that the thickness of a portion of said liquid crystal layer located on a region corresponding to said reflective region is substantially half the thickness of another portion of said liquid crystal layer located on another region corresponding to said transmissive region.

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13. The display according to claim 1, further comprising a thin-film transistor, formed between said insulating layer and said substrate, having a gate electrode, and

25 a storage capacitor having a storage capacitive

electrode, wherein

5 said reflective material layer having said function for serving as said reflective layer is constituted of a layer constituting said gate electrode and another layer constituting a storage capacitive line of said storage capacitive electrode.

10 14. The display according to claim 13, wherein said layer constituting said gate electrode and said layer constituting said storage capacitive line are formed by the same layer.

15 15. The display according to claim 1, further comprising a pixel electrode including said transparent electrode, wherein

 said pixel electrode is constituted of only said transparent electrode without including a reflective electrode.

20 16. The display according to claim 1, wherein said reflective material layer having said function for serving as said reflective layer consists of a plurality of layers.

25 17. A display, having a reflective region,

comprising:

a reflective material layer, formed on a region of a substrate corresponding to said reflective region, having a function for serving as a reflective layer;

5 an insulating layer formed on said reflective material layer; and

a transparent electrode formed on said insulating layer, wherein

10 said reflective material layer is formed by at least one layer selected from a group consisting of a source/drain electrode, a gate electrode, a storage capacitive electrode and a black matrix layer.

18. The display according to claim 17, wherein

15 said reflective material layer is formed by a layer constituting said gate electrode and said storage capacitive electrode.

19. A method of fabricating a display having a

20 reflective region, comprising steps of:

forming a reflective material layer also having a prescribed function different from a function for serving as a reflective layer on a substrate;

25 patterning said reflective material layer to be formed on a region corresponding to said reflective

region;

forming an insulating layer on said reflective material layer; and

5 forming a transparent electrode on said insulating layer.

20. The method of fabricating a display according to claim 19, further comprising a step of forming a thin-film transistor having a pair of source/drain regions between 10 said insulating layer and said substrate, wherein

said step of forming said reflective material layer includes a step of forming source/drain electrode layers connected to said pair of source/drain regions, and

15 said step of patterning said reflective material layer includes a step of patterning at least one of said source/drain electrode layers to be formed on a region corresponding to said source/drain regions and said reflective region.

20 21. The method of fabricating a display according to claim 19, further comprising a step of forming a storage capacitor having a storage capacitive electrode, wherein

said step of forming said reflective material layer includes a step of forming a layer constituting a storage 25 capacitive line of said storage capacitive electrode, and

said step of patterning said reflective material layer includes a step of patterning said layer constituting said storage capacitive line to be formed on said region corresponding to said reflective region.

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 22. The method of fabricating a display according to claim 19, further comprising a step of forming a thin-film transistor having a gate electrode between said insulating layer and said substrate, wherein

10 said step of forming said reflective material layer includes a step of forming a layer constituting said gate electrode, and

15 said step of patterning said reflective material layer includes a step of forming said layer constituting said gate electrode to be formed on said region corresponding to said reflective region.

20 23. The method of fabricating a display according to claim 19, further comprising a step of forming a thin-film transistor having a gate electrode and a storage capacitor having a storage capacitive electrode between said insulating layer and said substrate, wherein

25 said step of forming said reflective material layer includes a step of forming a first layer for defining a layer constituting said gate electrode and another layer

constituting a storage capacitive line of said storage capacitive electrode, and

5 said step of patterning said reflective material layer includes a step of patterning said first layer thereby forming said layer constituting said gate electrode and said layer constituting said storage capacitive line on said region corresponding to said reflective region.